# 1.8V Drive Nch+SBD MOSFET

# **QS5U34**

#### Structure

Silicon N-channel MOSFET Schottky Barrier DIODE

#### ● Features

- 1) The QS5U34 combines Nch MOSFET with a Schottky barrier diode in a single TSMT5 package.
- 2) Low on-state resistance with fast switching.
- 3) Low voltage drive (1.8V).
- 4) The Independently connected Schottky barrier diode has low forward voltage.

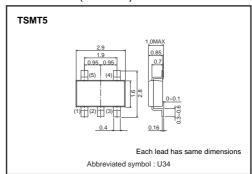
# Applications

Load switch, DC / DC conversion

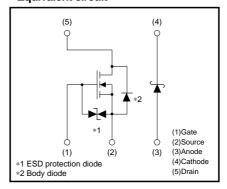
# Packaging specifications

|        | Package        | Taping |  |
|--------|----------------|--------|--|
| Туре   | Code           | TR     |  |
|        | Quantity (pcs) | 3000   |  |
| QS5U34 |                | 0      |  |

# ●Dimensions (Unit: mm)



### ●Equivalent circuit





# ● Absolute maximum ratings (Ta=25°C)

#### <MOSFET>

| Parameter                      | Symbol              | Limits             | Unit      |   |  |  |  |
|--------------------------------|---------------------|--------------------|-----------|---|--|--|--|
| Drain-source voltage           | V <sub>DSS</sub>    | 20                 | V         |   |  |  |  |
| Gate-source voltage            | V <sub>GSS</sub>    | 10                 | V         |   |  |  |  |
| Drain current                  | Continuous          | ΙD                 | ±1.5      | А |  |  |  |
| Drain current                  | Pulsed              | I <sub>DP</sub> *1 | ±3.0      | Α |  |  |  |
| Source current                 | Continuous          | Is                 | 0.6       | А |  |  |  |
| (Body diode)                   | Pulsed              | I <sub>SP</sub> *1 | 2.4       | А |  |  |  |
| Channel temperature            | Tch                 | 150                | °C        |   |  |  |  |
| Power dissipation              | P <sub>D</sub> *3   | 0.9                | W/ELEMENT |   |  |  |  |
| <di></di>                      |                     |                    |           |   |  |  |  |
| Repetitive peak reverse volta  | V <sub>RM</sub>     | 30                 | V         |   |  |  |  |
| Reverse voltage                | $V_R$               | 20                 | V         |   |  |  |  |
| Forward current                | l <sub>F</sub>      | 0.5                | А         |   |  |  |  |
| Forward current surge peak     | I <sub>FSM</sub> *2 | 2.0                | А         |   |  |  |  |
| Junction temperature           | Tj                  | 150                | °C        |   |  |  |  |
| Power dissipation              | P <sub>D</sub> *3   | 0.7                | W/ELEMENT |   |  |  |  |
| <mosfet and="" di=""></mosfet> |                     |                    |           |   |  |  |  |
| Total power dissipation        | P <sub>D</sub> *3   | 1.25               | W / TOTAL |   |  |  |  |
| Range of Storage temperatu     | Tstg                | -55 to +150        | °C        |   |  |  |  |

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 60Hz•1cyc. \*3 Mounted on a ceramic board

# ●Electrical characteristics (Ta=25°C)

# <MOSFET>

| Parameter                               | Symbol                 | Min. | Тур. | Max. | Unit      | Conditions                                   |  |
|---|------------------------|------|------|------|-----------|--|--|
| Gate-source leakage                     | Igss                   | -    | _    | 10   | μΑ        | V <sub>GS</sub> =10V / V <sub>DS</sub> =0V   |  |
| Drain-source breakdown voltage          | V <sub>(BR)</sub> DSS  | 20   | _    | _    | V         | I <sub>D</sub> =1mA, / V <sub>GS</sub> =0V   |  |
| Zero gate voltage drain current         | I <sub>DSS</sub>       | _    | _    | 1    | μΑ        | V <sub>DS</sub> =20V / V <sub>GS</sub> =0V   |  |
| Gate threshold voltage                  | VGS (th)               | 0.3  | _    | 1.3  | V         | Vps=10V / Ip=1mA                             |  |
| Out to the total out of the             |                        | _    | 130  | 180  | $m\Omega$ | I <sub>D</sub> =1.5A, V <sub>GS</sub> =4.5V  |  |
| Static drain-source on-state resistance | R <sub>DS (on)</sub> * | -    | 170  | 240  | mΩ        | I <sub>D</sub> =1.5A, V <sub>GS</sub> =2.5V  |  |
| 10313tai 10 <del>0</del>                |                        | _    | 220  | 310  | mΩ        | I <sub>D</sub> =0.8A, V <sub>GS</sub> =1.8V  |  |
| Forward transfer admittance             | Y <sub>fs</sub>   *    | 1.6  | _    | _    | S         | Vps=10V, Ip=1.5A                             |  |
| Input capacitance                       | Ciss                   | -    | 110  | _    | pF        | V <sub>DS</sub> =10V                         |  |
| Output capacitance                      | Coss                   | -    | 18   | _    | pF        | V <sub>GS</sub> =0V                          |  |
| Reverse transfer capacitance            | Crss                   | _    | 15   | -    | pF        | f=1MHz                                       |  |
| Turn-on delay time                      | <b>t</b> d (on) *      | -    | 5    | _    | ns        | Ip=1.0A                                      |  |
| Rise time                               | tr *                   | -    | 5    | _    | ns        | VDD≒10V                                      |  |
| Turn-off delay time                     | t <sub>d (off)</sub> * | _    | 20   | _    | ns        | V <sub>GS</sub> =4.5V<br>R <sub>L</sub> =10Ω |  |
| Fall time                               | t <sub>f</sub> *       | -    | 3    | -    | ns        | R <sub>G</sub> =10Ω                          |  |
| Total gate charge                       | Qg *                   | _    | 1.8  | 2.5  | nC        | V <sub>DD</sub> ≒10V                         |  |
| Gate-source charge                      | Q <sub>gs</sub> *      | _    | 0.3  | -    | nC        | V <sub>GS</sub> =4.5V                        |  |
| Gate-drain charge                       | Q <sub>gd</sub> *      | _    | 0.3  | _    | nC        | I <sub>D</sub> =1.5A                         |  |

### <MOSFET>Body diode (source-drain)

| Forward voltage | Vsp | _ | _ | 1.2 | V | I <sub>S</sub> =0.6A / V <sub>GS</sub> =0V |
|-----------------|-----|---|---|-----|---|--|

# <Di>

| Forward voltage | VF | _ | _ | 0.36 | V  | I <sub>F</sub> =0.1A |
|-----------------|----|---|---|------|----|----------------------|
|                 |    | _ | _ | 0.47 | V  | I <sub>F</sub> =0.5A |
| Reverse current | lR | _ | _ | 100  | μА | V <sub>R</sub> =20V  |



#### •Electrical characteristic curves

#### <MOSFET>

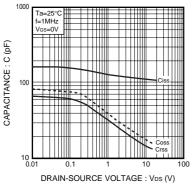


Fig.1 Typical Capacitance vs. Drain-Source Voltage

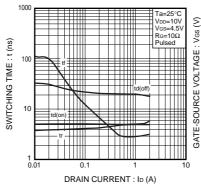


Fig.2 Switching Characteristics

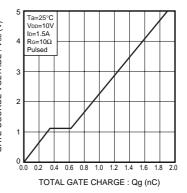


Fig.3 Dynamic Input Characteristics

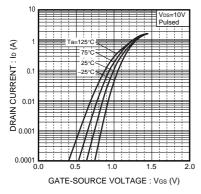


Fig.4 Typical Transfer Characteristics

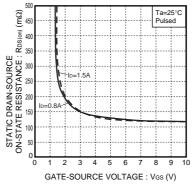


Fig.5 Static Drain-Source On-State Resistance vs. Gate-source Voltage

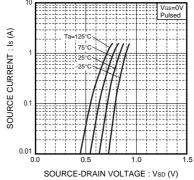


Fig.6 Source Current vs. Source-Drain Voltage

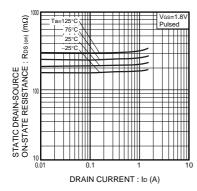


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current ( I )

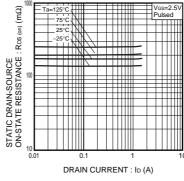


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current ( II )

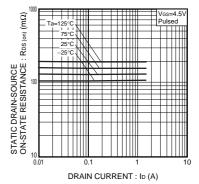
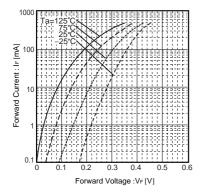


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current ( III )





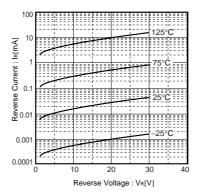


Fig.10 Forward Temperature Characteristics

Fig.11 Reverse Temperature Characteristics



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|---------|----------|------------|----------|--|
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| CLASSIV | CLASSIII | CLASSⅢ     |          |  |

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- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
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- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
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